

isc Silicon PNP Power Transistor

3CD4C

DESCRIPTION

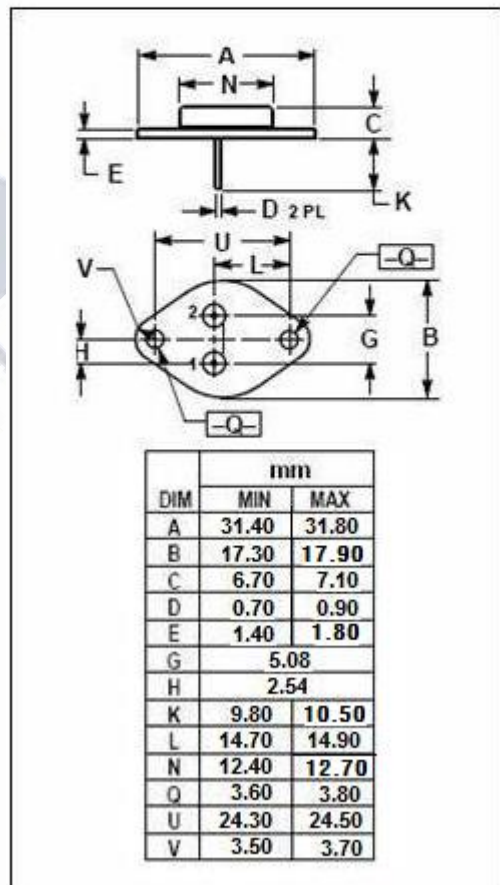
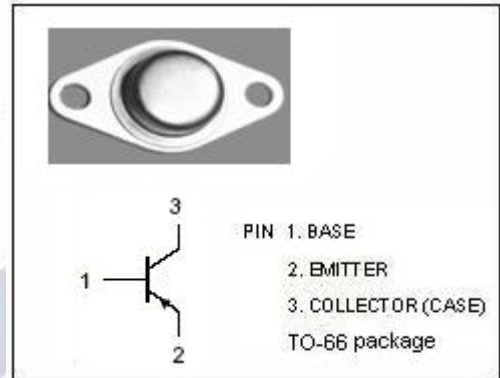
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -80V(\text{Min.})$
- DC Current Gain-
: $h_{FE} = 10-180 @ I_C = -1A$
- Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -1.5V(\text{Max}) @ I_C = -1A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power amplifier
- Low speed switching
- Power regulator

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-2	A
P_C	Collector Power Dissipation @ $T_C = 75^\circ C$	20	W
T_J	Junction Temperature	-55~150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$



isc Silicon PNP Power Transistor**3CD4C****ELECTRICAL CHARACTERISTICS**T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -5mA; I _B = 0	-80		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA; I _E = 0	-80		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -5mA; I _C = 0	-4		V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1A; I _B = -0.2A		-1.5	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -20V; I _B = 0		-2	mA
I _{CBO}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0		-10	μA
h _{FE}	DC Current Gain	I _C = -1A; V _{CE} = -10V	10	180	